

## Silicon NPN Power Transistors

## 2SC2615

## DESCRIPTION

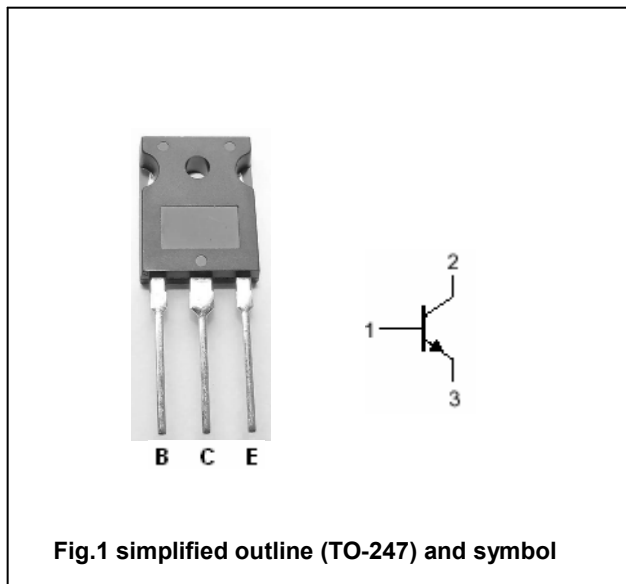
- With TO-247 package
- High voltage,high speed

## APPLICATIONS

- For high voltage,high speed and high power switching applications

## PINNING

| PIN | DESCRIPTION                          |
|-----|--------------------------------------|
| 1   | Base                                 |
| 2   | Collector;connected to mounting base |
| 3   | Emitter                              |

Absolute maximum ratings( $T_c=25^\circ\text{C}$ )

| SYMBOL    | PARAMETER                   | CONDITIONS             | VALUE   | UNIT             |
|-----------|-----------------------------|------------------------|---------|------------------|
| $V_{CBO}$ | Collector-base voltage      | Open emitter           | 500     | V                |
| $V_{CEO}$ | Collector-emitter voltage   | Open base              | 400     | V                |
| $V_{EBO}$ | Emitter-base voltage        | Open collector         | 7       | V                |
| $I_C$     | Collector current (DC)      |                        | 8       | A                |
| $P_C$     | Collector power dissipation | $T_C=25^\circ\text{C}$ | 80      | W                |
| $T_j$     | Junction temperature        |                        | 150     | $^\circ\text{C}$ |
| $T_{stg}$ | Storage temperature         |                        | -55~150 | $^\circ\text{C}$ |

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

| SYMBOL                | PARAMETER                            | CONDITIONS                               | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|------------------------------------------|-----|------|-----|------|
| V <sub>CEQ(SUS)</sub> | Collector-emitter sustaining voltage | I <sub>C</sub> =0.2A; I <sub>B</sub> =0  | 400 |      |     | V    |
| V <sub>(BR)EBO</sub>  | Emitter-base breakdown voltage       | I <sub>E</sub> =10mA; I <sub>C</sub> =0  | 7   |      |     | V    |
| V <sub>CEsat</sub>    | Collector-emitter saturation voltage | I <sub>C</sub> =4A; I <sub>B</sub> =0.8A |     |      | 1.0 | V    |
| V <sub>BEsat</sub>    | Base-emitter saturation voltage      | I <sub>C</sub> =4A; I <sub>B</sub> =0.8A |     |      | 1.5 | V    |
| I <sub>CBO</sub>      | Collector cut-off current            | V <sub>CB</sub> =400V; I <sub>E</sub> =0 |     |      | 0.1 | mA   |
| I <sub>EBO</sub>      | Emitter cut-off current              | V <sub>EB</sub> =5V; I <sub>C</sub> =0   |     |      | 0.1 | mA   |
| h <sub>FE-1</sub>     | DC current gain                      | I <sub>C</sub> =4A; V <sub>CE</sub> =5V  | 15  |      |     |      |
| h <sub>FE-2</sub>     | DC current gain                      | I <sub>C</sub> =8A; V <sub>CE</sub> =5V  | 7   |      |     |      |

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## PACKAGE OUTLINE

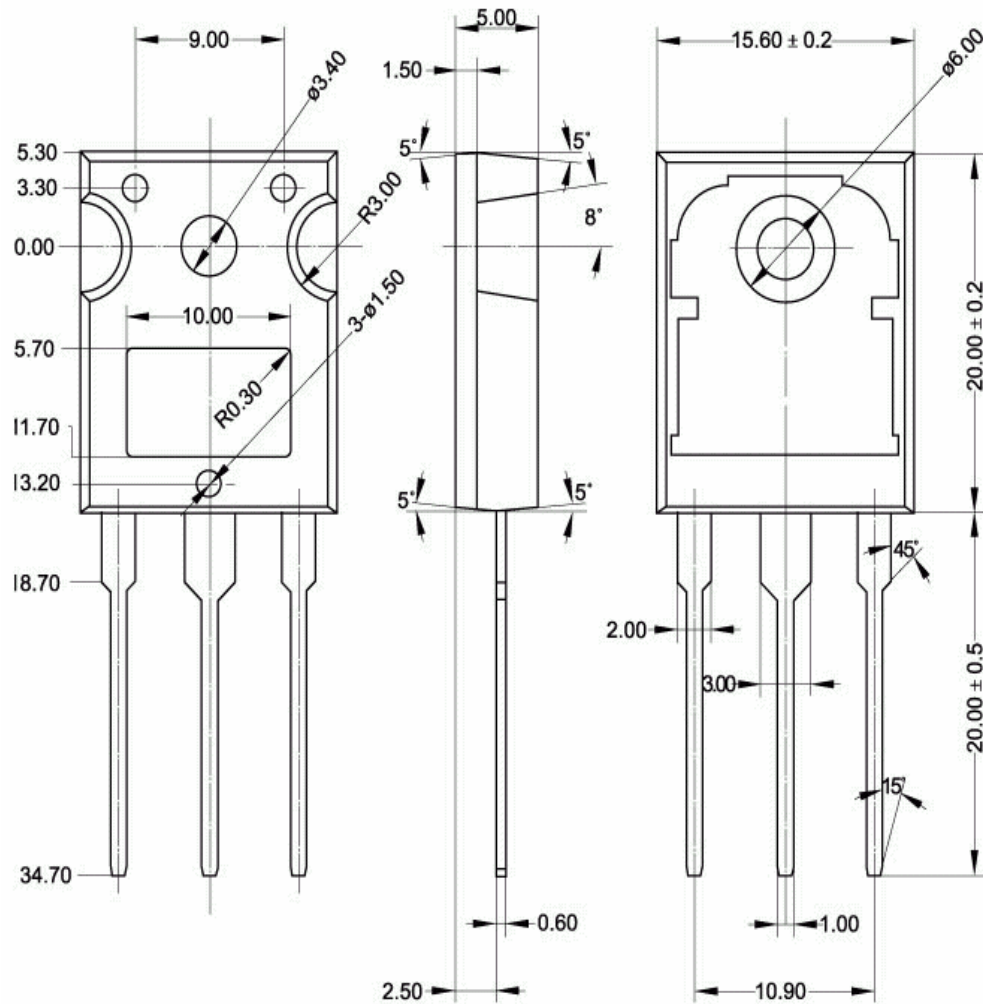


Fig.2 Outline dimensions